

2SC5622

Silicon NPN triple diffusion mesa type

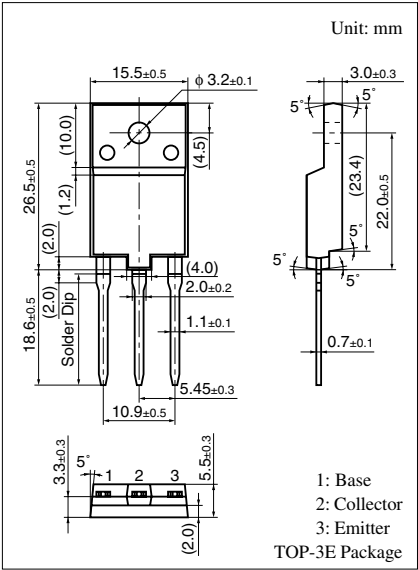
For horizontal deflection output

■ Features

- High breakdown voltage: 1 500 V
- High-speed switching
- Wide area of safe operation (ASO)

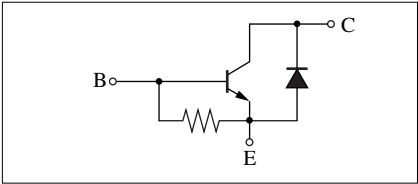
■ Absolute Maximum Ratings $T_C = 25^{\circ}\text{C}$

Parameter		Symbol	Rating	Unit
Collector to base voltage		V_{CBO}	1 500	V
Collector to emitter voltage		V_{CES}	1 500	V
Emitter to base voltage		V_{EBO}	7	V
Peak collector current		I_{CP}	12	A
Collector current		I_C	6	A
Base current		I_B	3	A
Collector power dissipation	$T_C = 25^{\circ}\text{C}$	P_C	40	W
	$T_a = 25^{\circ}\text{C}$		3	
Junction temperature		T_j	150	$^{\circ}\text{C}$
Storage temperature		T_{stg}	-55 to +150	$^{\circ}\text{C}$



Marking Symbol: C5622

Internal Connection



■ Electrical Characteristics $T_C = 25^{\circ}\text{C} \pm 3^{\circ}\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = 1\,000\text{ V}, I_E = 0$			50	μA
		$V_{CB} = 1\,500\text{ V}, I_E = 0$			1	mA
Emitter to base voltage	V_{EBO}	$I_E = 500\text{ mA}, I_C = 0$			7	V
Forward current transfer ratio	h_{FE}	$V_{CE} = 5\text{ V}, I_C = 4\text{ A}$	5		9	
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = 4\text{ A}, I_B = 0.8\text{ A}$			5	V
Base to emitter saturation voltage	$V_{BE(sat)}$	$I_C = 4\text{ A}, I_B = 0.8\text{ A}$			1.5	V
Transition frequency	f_T	$V_{CE} = 10\text{ V}, I_C = 0.1\text{ A}, f = 0.5\text{ MHz}$		3		MHz
Diode forward voltage	V_F	$I_F = 4\text{ A}$			-2	V
Storage time	t_{stg}	$I_C = 4\text{ A}, \text{Resistance loaded}$			5.0	μs
Fall time	t_f	$I_{B1} = 0.8\text{ A}, I_{B2} = -1.6\text{ A}$			0.5	μs